2024/ 001

SIKA e-SiC® 5N
Product information

High purity silicon carbide powders for semiconductor and electronic applications.

High purity silicon carbide produced by the Acheson process for semiconductor and electronic applications. Particularly suitable for PVT crystal growth for SiC wafer manufacturing.

Typical chemistry

Element	Concentration [ppm wt]	Element	Concentration [ppm wt]
Al	1,5	**Ni**	0.1
B	0.23	**S**	0,5
Cr	<0,3	**Ti**	1,5
Cu	0.1	**V**	0.1
Fe	1.0	**Zn**	0.1
Li	<0,05		

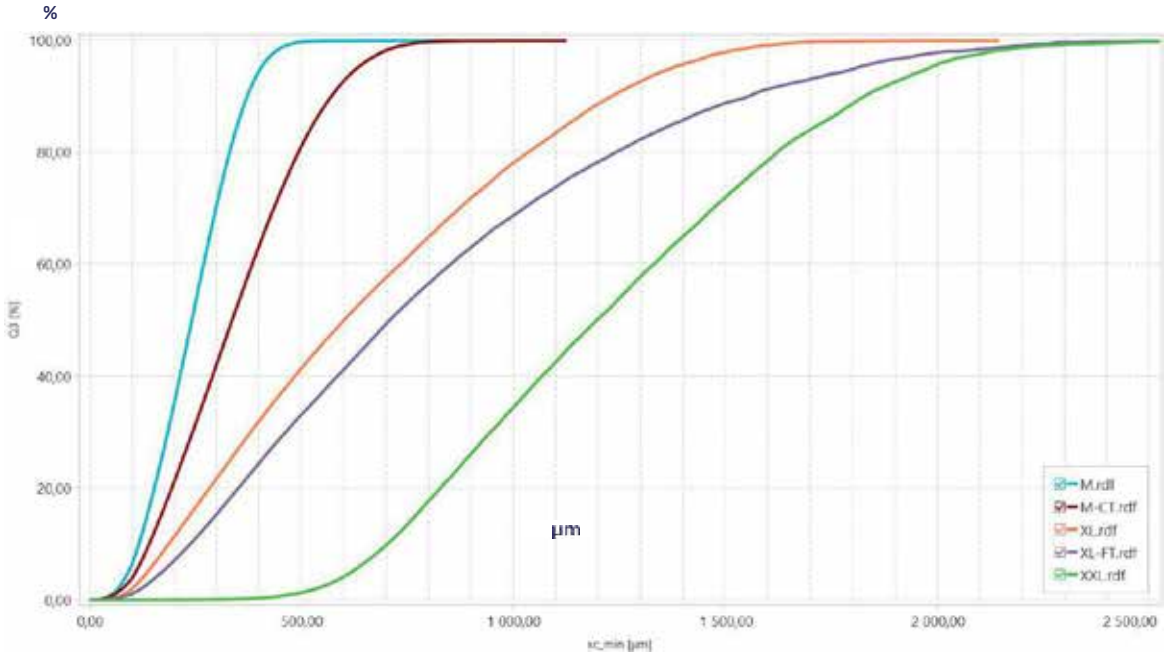
Analysis by GDMS

Element	Measurement	Unit	Instrument/methode
Free C	0.01	% wt	Carbolite
Free Si	0.04	% wt	ANSI B74.15
Total oxygen	0.01	% wt	LECO

Particle size distribution, Size classes (µm)

M	106-200	200-300	300-450
M-CT	106-300	300-450	450-710
XL	106-710	710-1100	1100-1700
XXL	710-1400	1400-2000	2000-2500
XL-FT	106-710	710-1700	1700-2500

Typical particle size distribution curve (Camsizer)



SIKA Silicon Carbide